

IN THE ABSTRACT:

Please amend the abstract as follows:

ABSTRACT

~~The present invention relates to~~ [[a]] A semiconductor memory device in which information is written into a storage element by flowing current. The semiconductor memory device has a ~~The invention aims at shortening~~ shortened write speed and reduced ~~reducing~~ power consumption by preventing parasitic capacitors from prolonging the time required for a write current to reach a predetermined value. ~~The apparatus~~ semiconductor memory device includes storage elements for storing information, a constant current source for writing information into the storage element by flowing current, and a boost circuit for charging parasitic capacitors by a time when an amount of a current flowed by ~~said~~ the constant current source reaches an amount of a current required to write information into the storage element, at a predetermined position related to the storage element.